

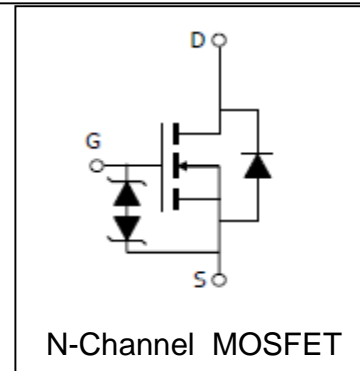
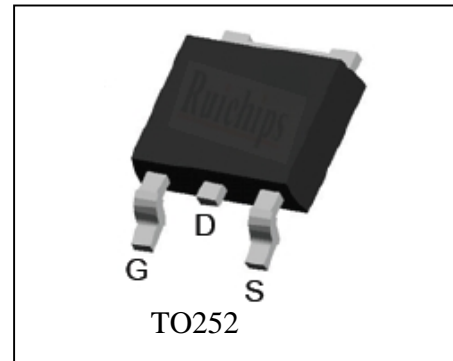
Features

- 30V/60A,
 $R_{DS(ON)} = 5m$ (Typ.)@ $V_{GS}=10V$
 $R_{DS(ON)} = 10m$ (Typ.)@ $V_{GS}=4.5V$
- Super High Dense Cell Design
- ESD protected
- Reliable and Rugged
- 100% avalanche tested
- Lead Free and Green Devices Available
 (RoHS Compliant)

Applications

- Power Management.

Pin Description



Absolute Maximum Ratings

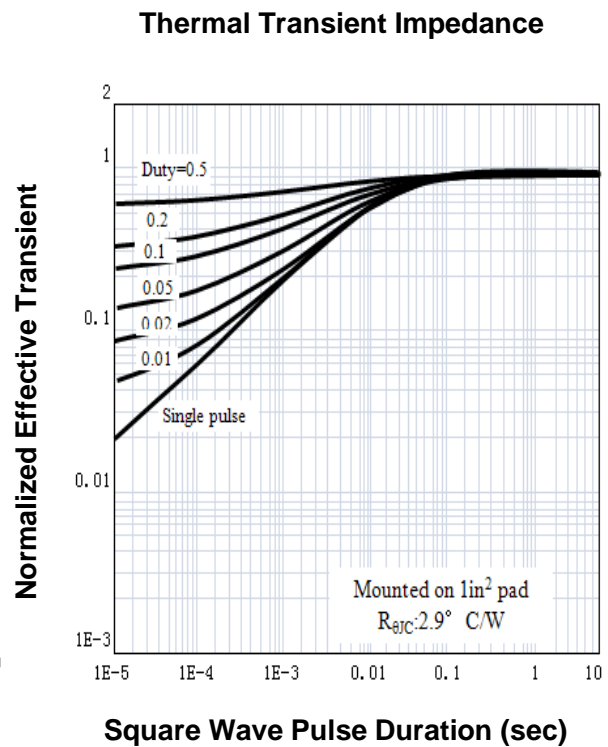
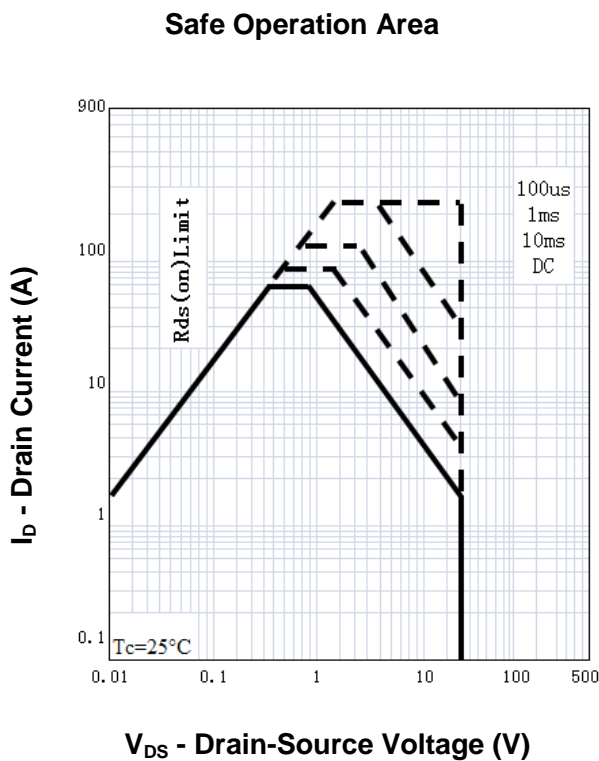
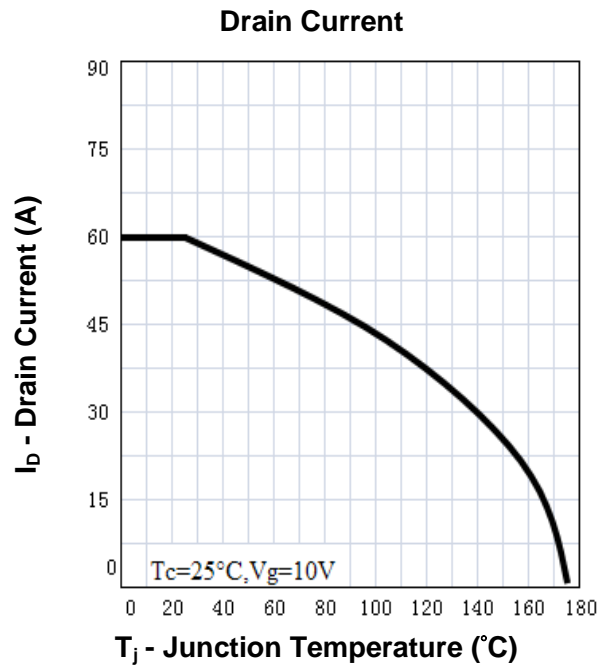
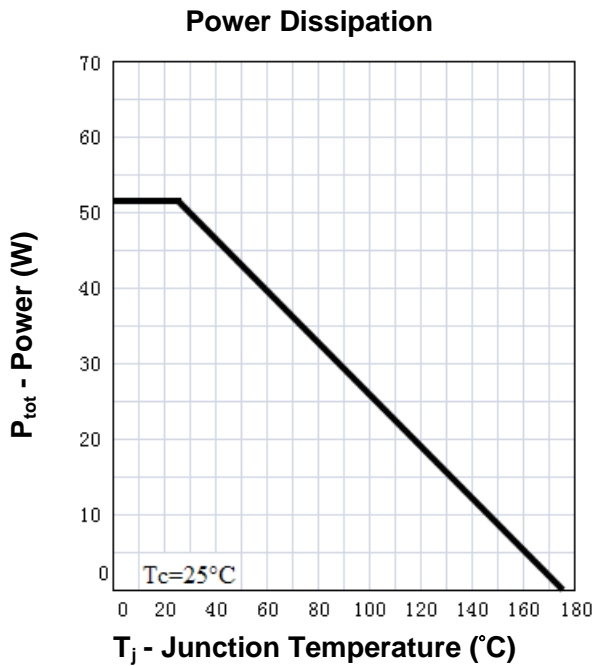
Symbol	Parameter	Rating	Unit
Common Ratings ($T_C=25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 16	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$ 60 ^①	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C=25^\circ C$ 240 ^②	A
I_D	Continuous Drain Current($V_{GS}=10V$)	$T_C=25^\circ C$ 60 ^①	A
		$T_C=100^\circ C$ 43 ^①	
P_D	Maximum Power Dissipation	$T_C=25^\circ C$ 52	W
		$T_C=100^\circ C$ 26	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.9	$^\circ C/W$
Drain-Source Avalanche Ratings			
E_{AS} ^③	Avalanche Energy, Single Pulsed	100	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU30E40L			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1	μA
					30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1		2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=20A$		5	7	$m\Omega$
		$V_{GS}=4.5V, I_{DS}=14A$		10	15	$m\Omega$
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=20A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=20A, dI_{SD}/dt=100A/\mu s$		32		ns
Q_{rr}	Reverse Recovery Charge			64		nC
Dynamic Characteristics ⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.6		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=15V,$ Frequency=1.0MHz		860		pF
C_{oss}	Output Capacitance			100		
C_{rss}	Reverse Transfer Capacitance			60		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=15V, R_L=0.75\Omega,$ $I_{DS}=20A, V_{GEN}=10V,$ $R_G=6\Omega$		10		ns
t_r	Turn-on Rise Time			12		
$t_{d(OFF)}$	Turn-off Delay Time			25		
t_f	Turn-off Fall Time			13		
Gate Charge Characteristics ⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=24V, V_{GS}=10V,$ $I_{DS}=20A$		24		nC
Q_{gs}	Gate-Source Charge			7		
Q_{gd}	Gate-Drain Charge			9		

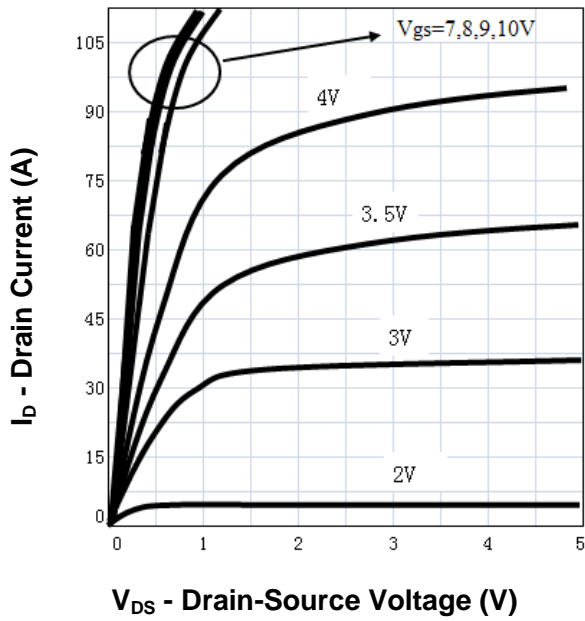
- Notes: ① Calculated continuous current based on maximum allowable junction temperature. The current limitation by source bonding is 30A.
 ② Pulse width limited by safe operating area.
 ③ Limited by $T_{Jmax}, I_{AS}=20A, V_{DD}=24V, R_G=50\Omega$, Starting $T_J=25^\circ\text{C}$.
 ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

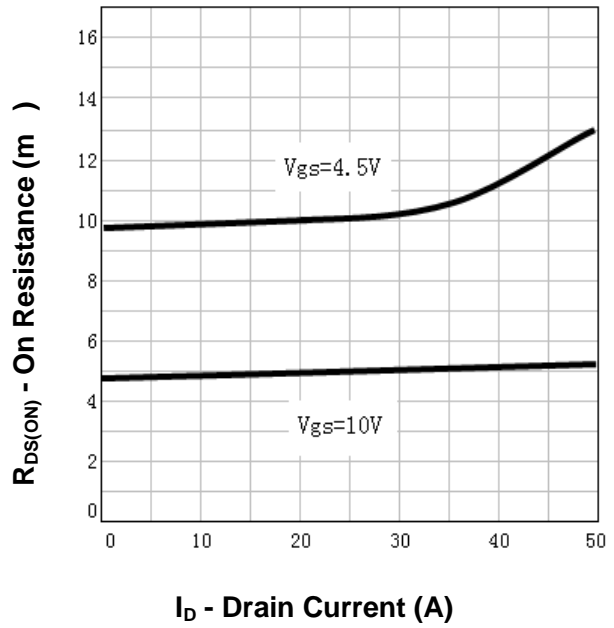


Typical Characteristics

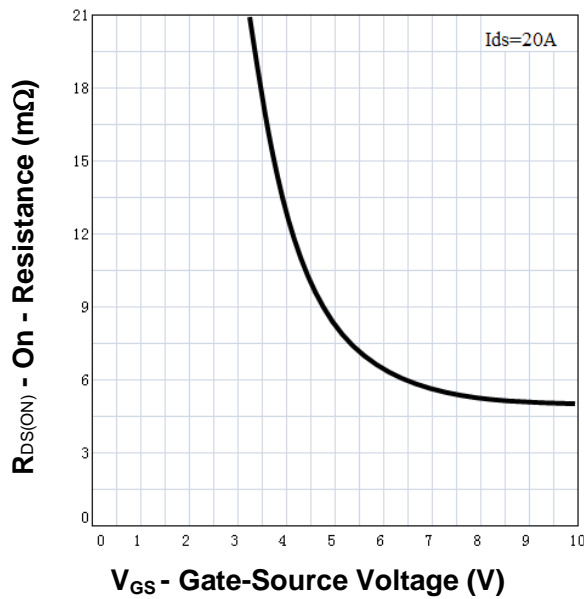
Output Characteristics



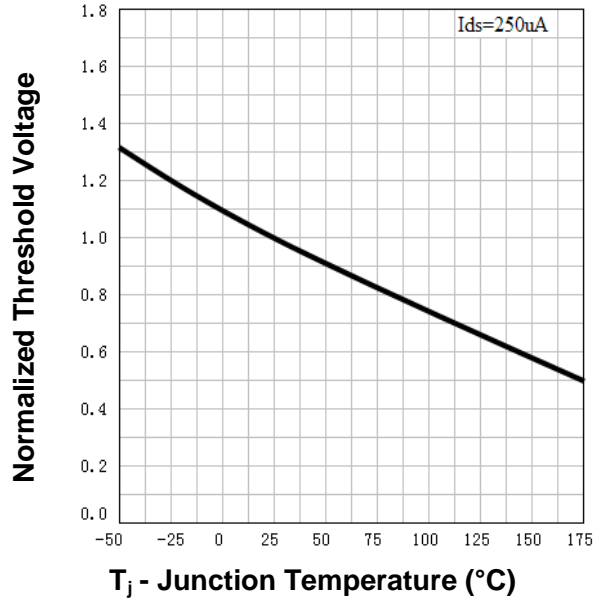
Drain-Source On Resistance



Drain-Source On Resistance

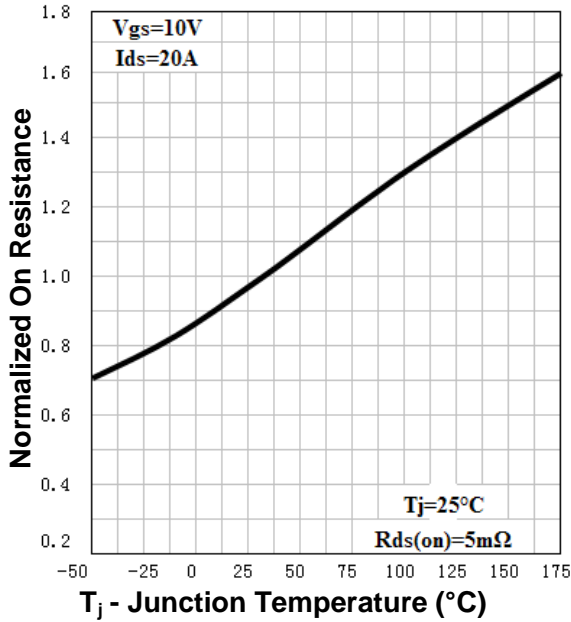


Gate Threshold Voltage

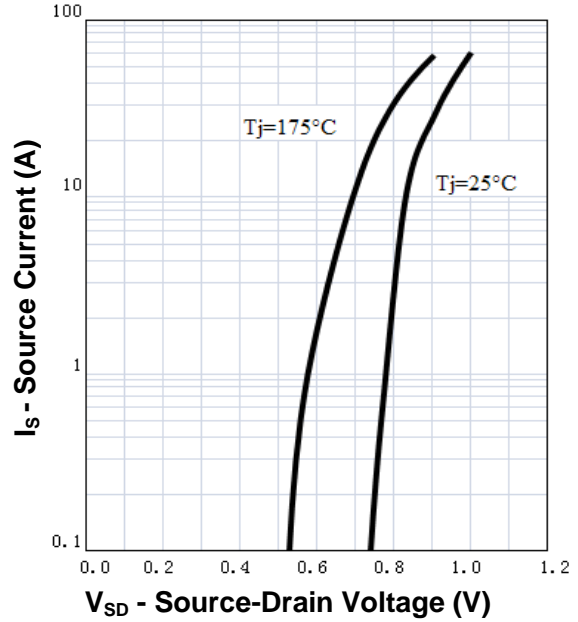


Typical Characteristics

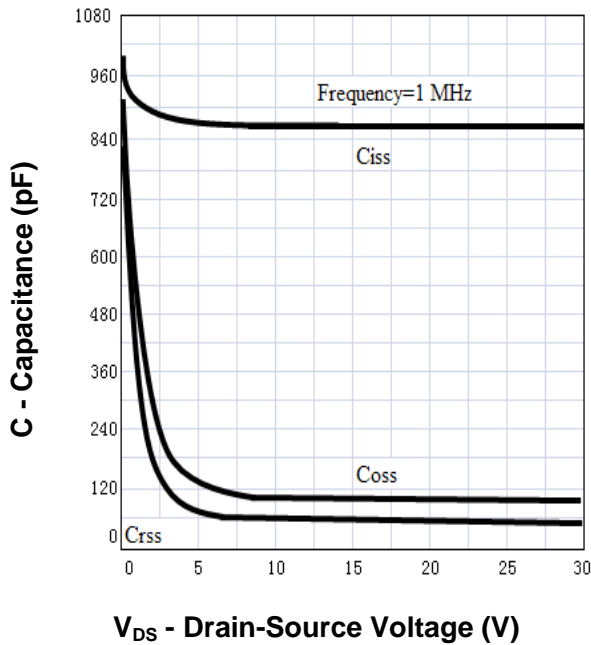
Drain-Source On Resistance



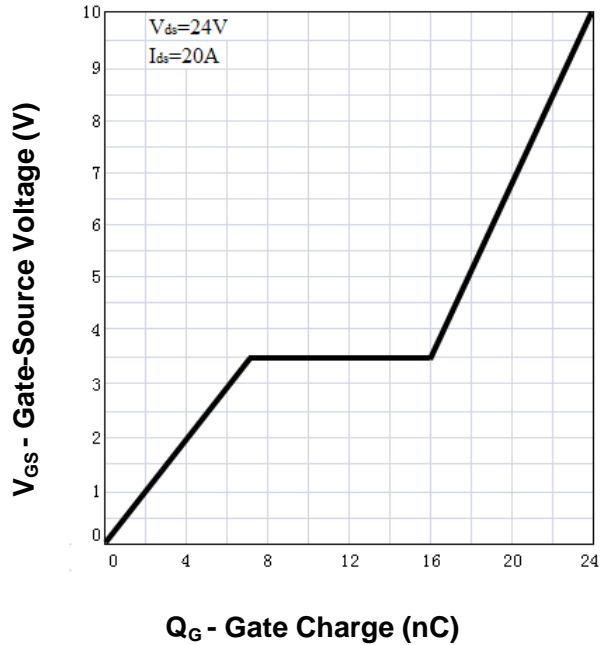
Source-Drain Diode Forward



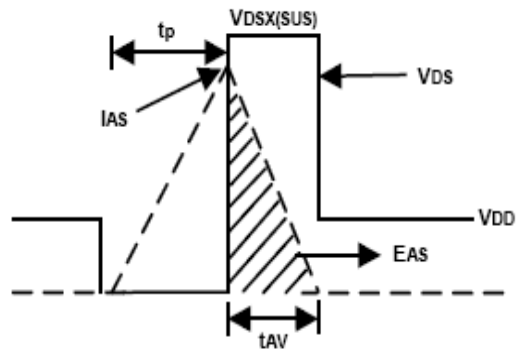
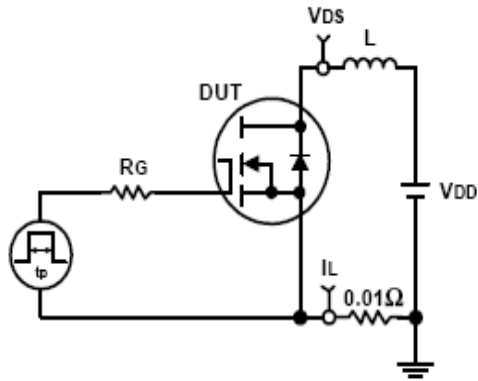
Capacitance



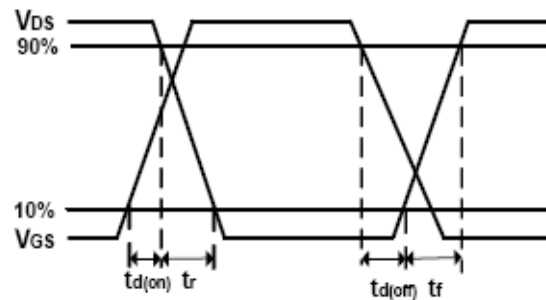
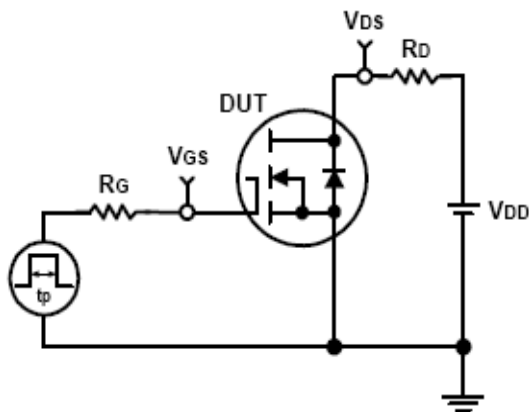
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

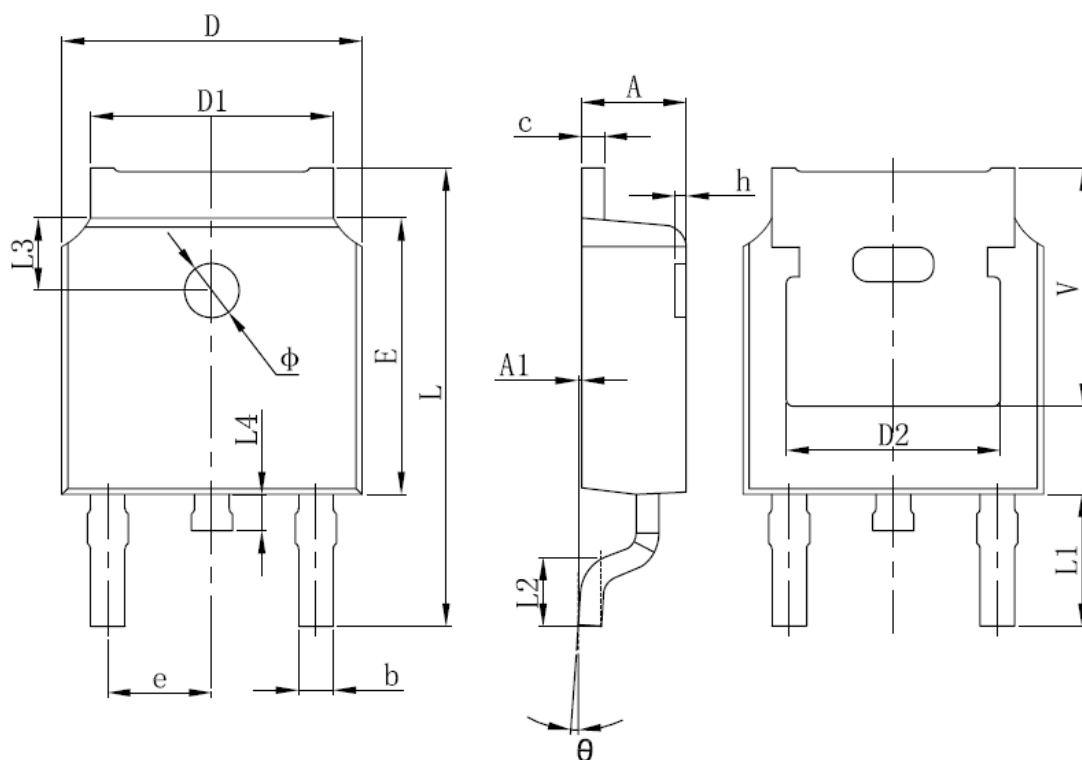


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU30E40L	RU30E40L	TO-252	Tape&Reel	2500	13''	16mm

Package Information

TO252-2L



SYMBOL	MM		INCH		SYMBOL	MM		INCH	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	2.200	2.400	0.087	0.094	L	9.800	10.400	0.386	0.409
A1	0.000	0.127	0.000	0.005	L1	2.900 REF.		0.114 REF.	
b	0.660	0.860	0.026	0.034	L2	1.400	1.700	0.055	0.067
C	0.460	0.580	0.018	0.023	L3	1.600 REF.		0.063 REF.	
D	6.500	6.700	0.256	0.264	L4	0.600	1.000	0.024	0.039
D1	5.100	5.460	0.201	0.215	Φ	1.100	1.300	0.043	0.051
D2	4.830 REF.		0.190 REF.		θ	0°	8°	0°	8°
E	6.000	6.200	0.236	0.244	h	0.000	0.300	0.000	0.012
e	2.186	2.386	0.086	0.094	V	5.350 REF.		0.211 REF.	

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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